

IR2125

CURRENT LIMITING SINGLE CHANNEL DRIVER

Features

- Floating channel designed for bootstrap operation
 Fully operational to +500V
 Tolerant to negative transient voltage
 dV/dt immune
- Gate drive supply range from 12 to 18V
- Undervoltage lockout
- Current detection and limiting loop to limit driven power transistor current
- Error lead indicates fault conditions and programs shutdown time
- Output in phase with input

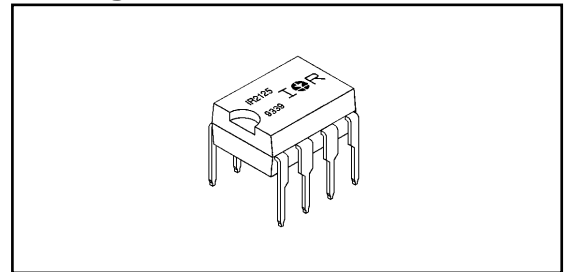
Description

The IR2125 is a high voltage, high speed power MOSFET and IGBT driver with over-current limiting protection circuitry. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. Logic inputs are compatible with standard CMOS or LSTTL outputs. The output driver features a high pulse current buffer stage designed for minimum driver cross-conduction. The protection circuitry detects over-current in the driven power transistor and limits the gate drive voltage. Cycle by cycle shutdown is programmed by an external capacitor which directly controls the time interval between detection of the over-current limiting conditions and latched shut-

Product Summary

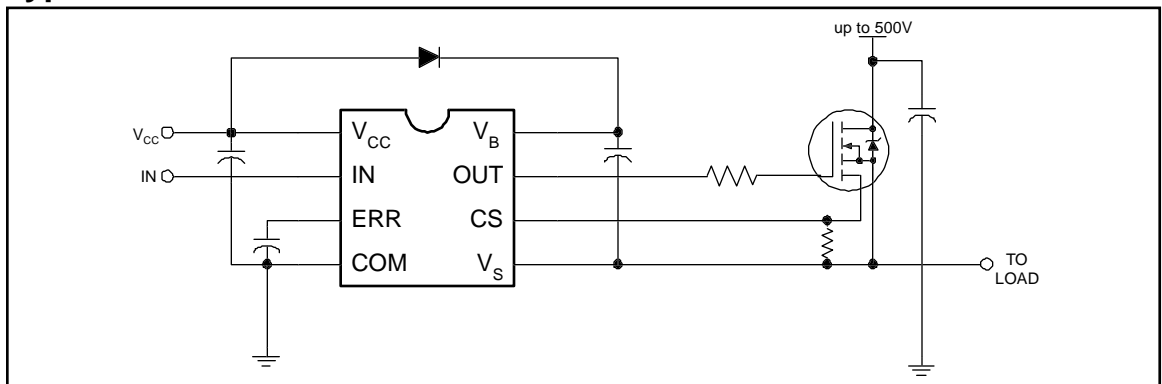
V_{OFFSET}	500V max.
$I_{\text{O+/-}}$	1A / 2A
V_{OUT}	12 - 18V
V_{Csth}	230 mV
$t_{\text{on/off (typ.)}}$	150 & 150 ns

Package



down. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high or low side configuration which operates up to 500 volts.

Typical Connection



Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Parameter Definition	Value		Units
		Min.	Max.	
V _B	High Side Floating Supply Voltage	-0.3	525	V
V _S	High Side Floating Offset Voltage	V _B - 25	V _B + 0.3	
V _{HO}	High Side Floating Output Voltage	V _S - 0.3	V _B + 0.3	
V _{CC}	Logic Supply Voltage	-0.3	25	
V _{IN}	Logic Input Voltage	-0.3	V _{CC} + 0.3	
V _{ERR}	Error Signal Voltage	-0.3	V _{CC} + 0.3	
V _{CS}	Current Sense Voltage	V _S - 0.3	V _B + 0.3	
dV _S /dt	Allowable Offset Supply Voltage Transient	—	50	V/ns
P _D	Package Power Dissipation @ T _A ≤ +25°C	—	1.0	W
R _{θJA}	Thermal Resistance, Junction to Ambient	—	125	°C/W
T _J	Junction Temperature	—	150	°C
T _S	Storage Temperature	-55	150	
T _L	Lead Temperature (Soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Parameter Definition	Value		Units
		Min.	Max.	
V _B	High Side Floating Supply Voltage	V _S + 12	V _S + 18	V
V _S	High Side Floating Offset Voltage	Note 1	500	
V _{HO}	High Side Floating Output Voltage	V _S	V _B	
V _{CC}	Logic Supply Voltage	0	18	
V _{IN}	Logic Input Voltage	0	V _{CC}	
V _{ERR}	Error Signal Voltage	0	V _{CC}	
V _{CS}	Current Sense Signal Voltage	V _S	V _B	
T _A	Ambient Temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +500V. Logic state held for V_S of -5V to -V_{BS}.

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V, C_L = 3300 pF and T_A = 25°C unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Figures 3 through 6.

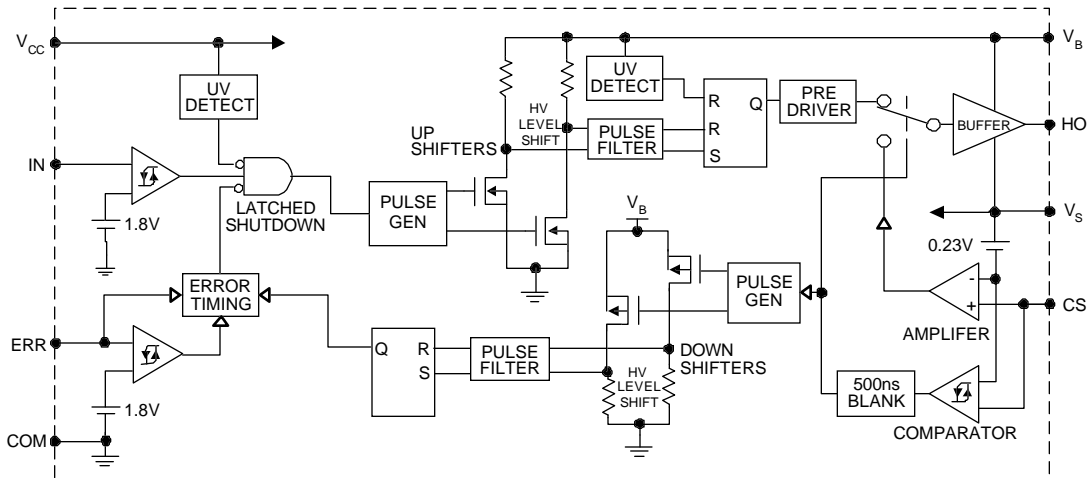
Symbol	Parameter Definition	Figure	Value			Units	Test Conditions
			Min.	Typ.	Max.		
t_{on}	Turn-On Propagation Delay	7	—	150	200	ns	
t_{off}	Turn-Off Propagation Delay	8	—	150	190		
t_{sd}	ERR Shutdown Propagation Delay	9	—	1.7	2.2	μ s	
t_r	Turn-On Rise Time	10	—	43	60	ns	
t_f	Turn-Off Fall Time	11	—	26	35		
t_{cs}	CS Shutdown Propagation Delay	12	—	0.7	1.2	μ s	$C_{ERR} = 270$ pF
t_{err}	CS to ERR Pull-Up Propagation Delay	13	—	9.0	12		

Static Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to V_S .

Symbol	Parameter Definition	Figure	Value			Units	Test Conditions	
			Min.	Typ.	Max.			
V_{IH}	Logic "1" Input Voltage	14	2.2	—	—	V	$V_{CC} = 12V$ to 18V	
V_{IL}	Logic "0" Input Voltage	15	—	—	0.8		$V_{CC} = 12V$ to 18V	
V_{CSTH+}	CS Input Positive Going Threshold	16	150	230	320	mV	$V_{CC} = 12V$ to 18V	
V_{CSTH-}	CS Input Negative Going Threshold	17	130	200	260		$V_{CC} = 12V$ to 18V	
V_{OH}	High Level Output Voltage, $V_{BIAS} - V_O$	18	—	—	100	mV	$I_O = 0A$	
V_{OL}	Low Level Output Voltage, V_O	19	—	—	100		$I_O = 0A$	
I_{LK}	Offset Supply Leakage Current	20	—	—	50	μ A	$V_B = V_S = 500V$	
I_{QBS}	Quiescent V_{BS} Supply Current	21	—	400	1000		$V_{IN} = V_{CS} = 0V$ or 5V	
I_{QCC}	Quiescent V_{CC} Supply Current	22	—	700	1200		$V_{IN} = V_{CS} = 0V$ or 5V	
I_{IN+}	Logic "1" Input Bias Current	23	—	4.5	10		$V_{IN} = 5V$	
I_{IN-}	Logic "0" Input Bias Current	24	—	—	1.0		$V_{IN} = 0V$	
I_{CS+}	"High" CS Bias Current	25	—	4.5	10		$V_{CS} = 3V$	
I_{CS-}	"Low" CS Bias Current	26	—	—	1.0		$V_{CS} = 0V$	
V_{BSUV+}	V_{BS} Supply Undervoltage Positive Going Threshold	27	8.5	9.2	10.0		V	
V_{BSUV-}	V_{BS} Supply Undervoltage Negative Going Threshold	28	7.7	8.3	9.0			
V_{CCUV+}	V_{CC} Supply Undervoltage Positive Going Threshold	29	8.3	8.9	9.6			
V_{CCUV-}	V_{CC} Supply Undervoltage Negative Going Threshold	30	7.3	8.0	8.7			
I_{ERR}	ERR Timing Charge Current	31	65	100	130	μ A	$V_{IN} = 5V$, $V_{CS} = 3V$ $ERR < V_{ERR+}$	
I_{ERR+}	ERR Pull-Up Current	32	8.0	15	—	mA	$V_{IN} = 5V$, $V_{CS} = 3V$ $ERR > V_{ERR+}$	
I_{ERR-}	ERR Pull-Down Current	33	16	30	—		$V_{IN} = 0V$	
I_{O+}	Output High Short Circuit Pulsed Current	34	1.0	1.6	—	A	$V_O = 0V$, $V_{IN} = 5V$ $PW \leq 10$ μ s	
I_{O-}	Output Low Short Circuit Pulsed Current	35	2.0	3.3	—		$V_O = 15V$, $V_{IN} = 0V$ $PW \leq 10$ μ s	

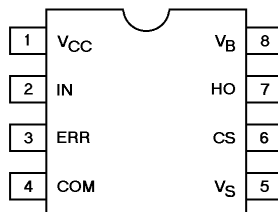
Functional Block Diagram



Lead Definitions

Symbol	Description
V _{CC}	Logic and gate drive supply
IN	Logic input for gate driver output (HO), in phase with HO
ERR	Serves multiple functions; status reporting, linear mode timing and cycle by cycle logic shutdown
COM	Logic ground
V _B	High side floating supply
HO	High side gate drive output
V _S	High side floating supply return
CS	Current sense input to current sense comparator

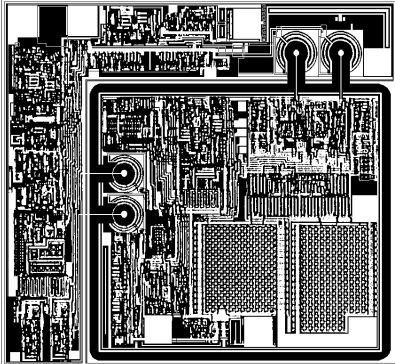
Lead Assignments



IR2125

Part Number

Device Information

Process & Design Rule		HVDCMOS 4.0 μ m
Transistor Count		410
Die Size		104 X 111 X 26 (mil)
Die Outline		
Thickness of Gate Oxide		800Å
Connections	Material	Poly Silicon
	Width	4 μ m
First Layer	Spacing	6 μ m
	Thickness	5000Å
	Material	Al - Si (Si: 1.0% \pm 0.1%)
Second Layer	Width	6 μ m
	Spacing	9 μ m
	Thickness	20,000Å
Contact Hole Dimension		8 μ m X 8 μ m
Insulation Layer	Material	PSG (SiO ₂)
	Thickness	1.5 μ m
Passivation (1)	Material	PSG (SiO ₂)
	Thickness	1.5 μ m
Passivation (2)	Material	Proprietary*
	Thickness	Proprietary*
Method of Saw		Full Cut
Method of Die Bond		Ablebond 84 - 1
Wire Bond	Method	Thermo Sonic
	Material	Au (1.0 mil / 1.3 mil)
Leadframe	Material	Cu
	Die Area	Ag
	Lead Plating	Pb : Sn (37 : 63)
Package	Types	8 Lead PDIP
	Materials	EME6300 / MP150 / MP190
Remarks: * Patent Pending		

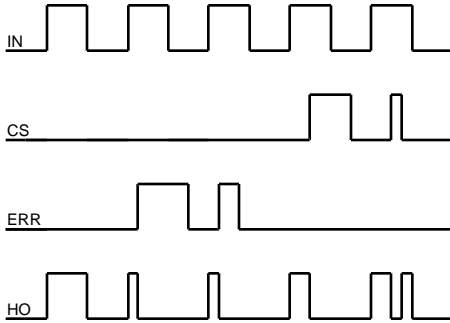


Figure 1. Input/Output Timing Diagram

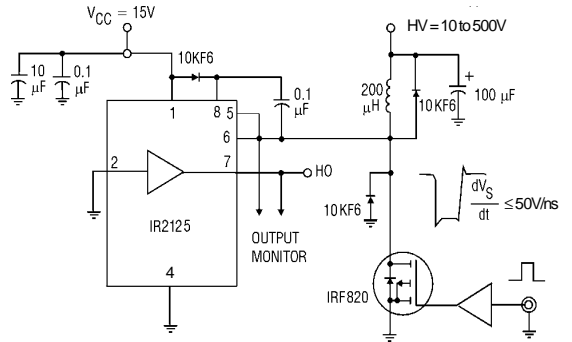


Figure 2. Floating Supply Voltage Transient Test Circuit

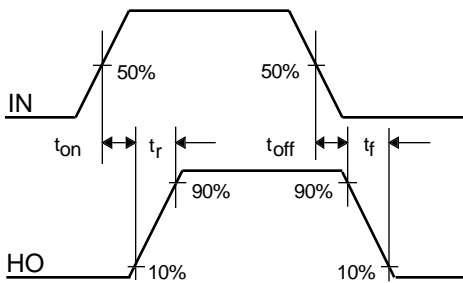


Figure 3. Switching Time Waveform Definitions

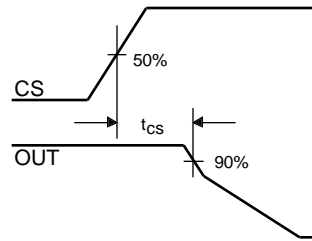


Figure 4. ERR Shutdown Waveform Definitions

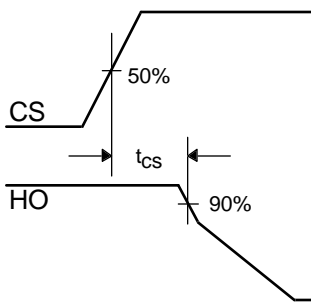


Figure 5. CS Shutdown Waveform Definitions

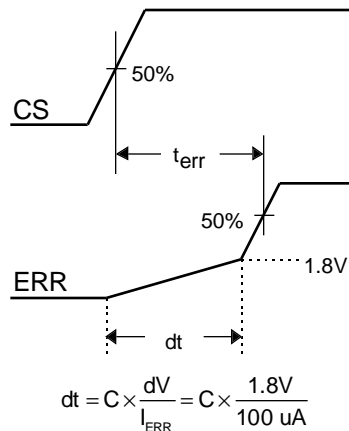


Figure 6. CS to ERR Waveform Definitions

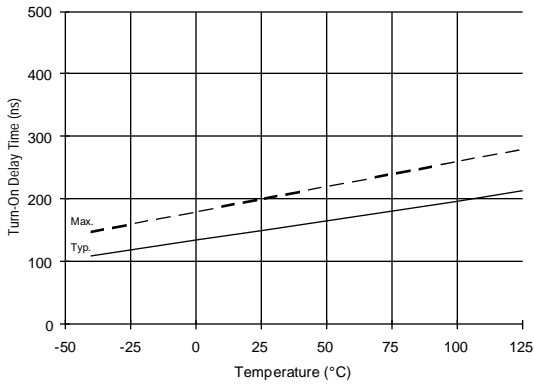


Figure 7A. Turn-On Time vs. Temperature

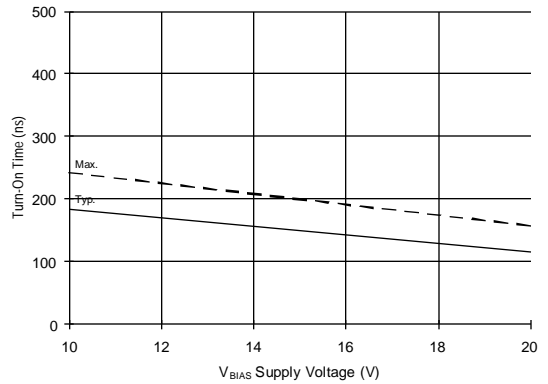


Figure 7B. Turn-On Time vs. Voltage

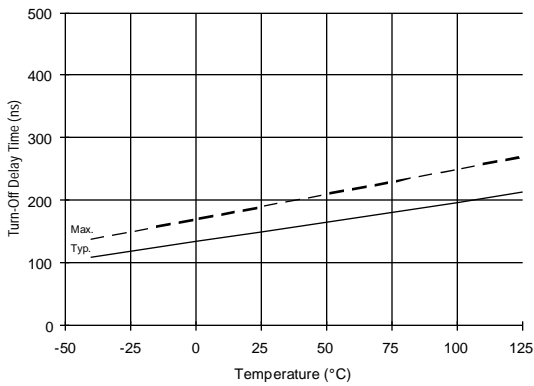


Figure 8A. Turn-Off Time vs. Temperature

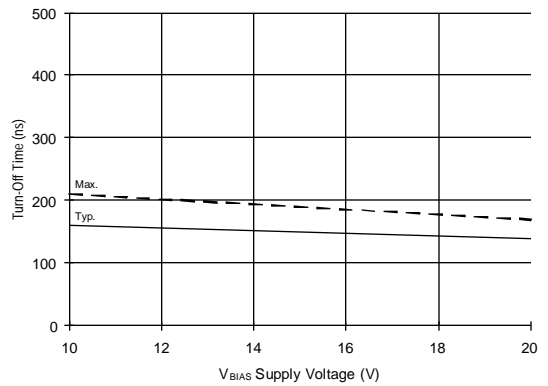


Figure 8B. Turn-Off Time vs. Voltage

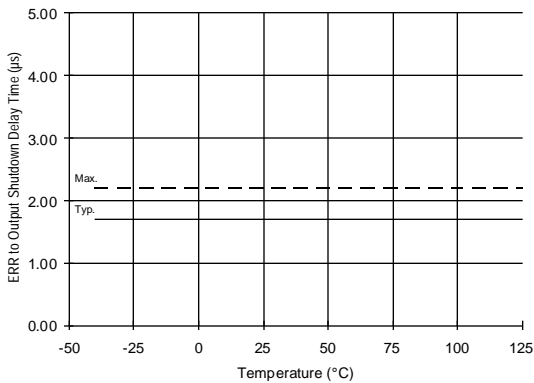


Figure 9A. ERR to Output Shutdown vs. Temperature

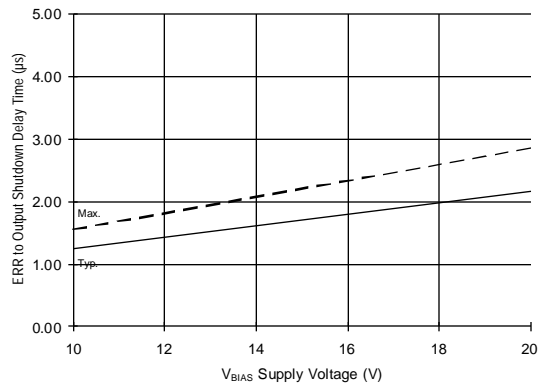


Figure 9B. ERR to Output Shutdown vs. Voltage

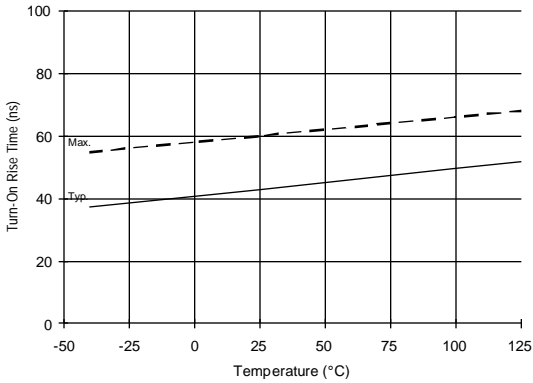


Figure 10A. Turn-On Rise Time vs. Temperature

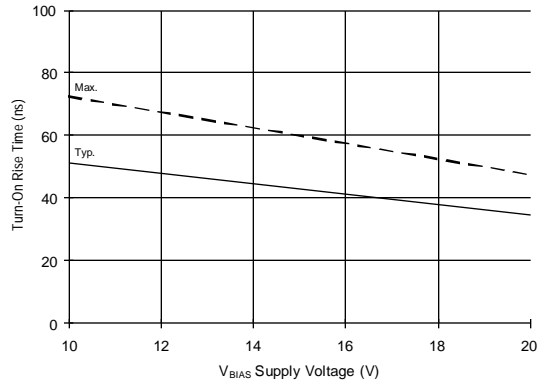


Figure 10B. Turn-On Rise Time vs. Voltage

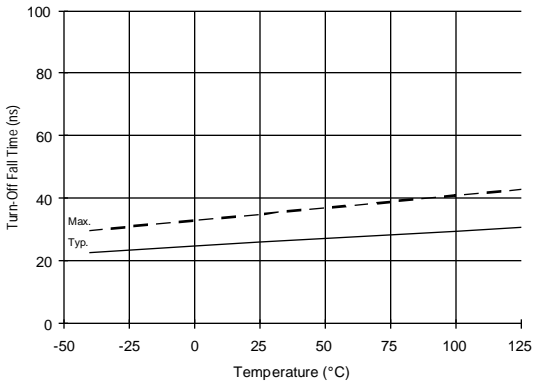


Figure 11A. Turn-Off Fall Time vs. Temperature

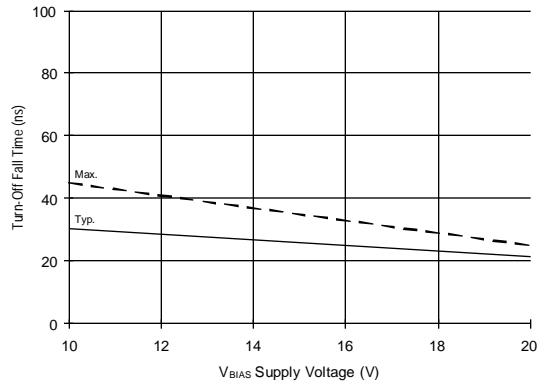


Figure 11B. Turn-Off Fall Time vs. Voltage

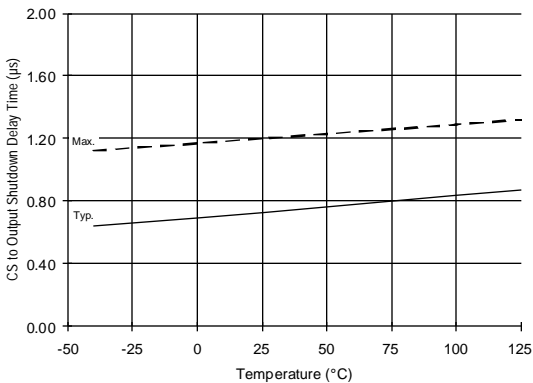


Figure 12A. CS to Output Shutdown vs. Temperature

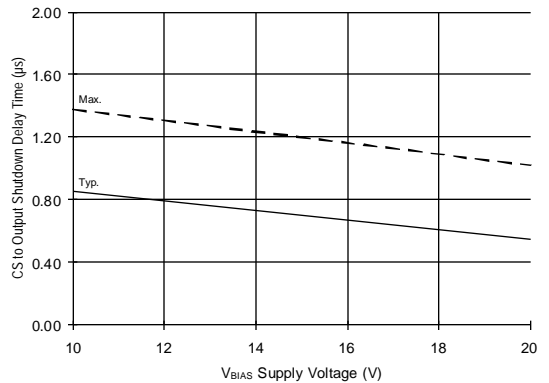


Figure 12B. CS to Output Shutdown vs. Voltage

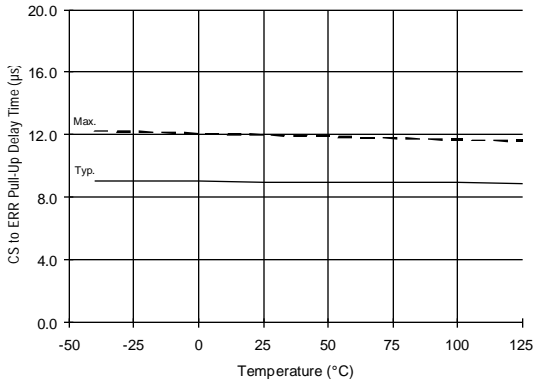


Figure 13A. CS to ERR Pull-Up vs. Temperature

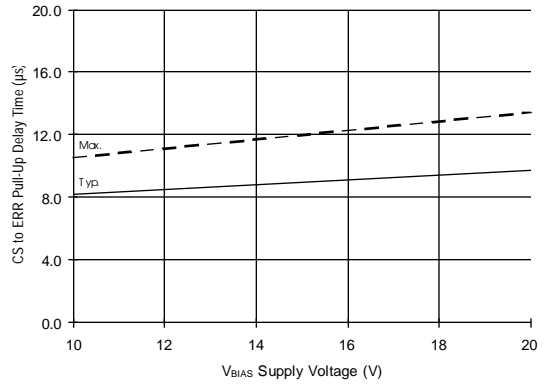


Figure 13B. CS to ERR Pull-Up vs. Voltage

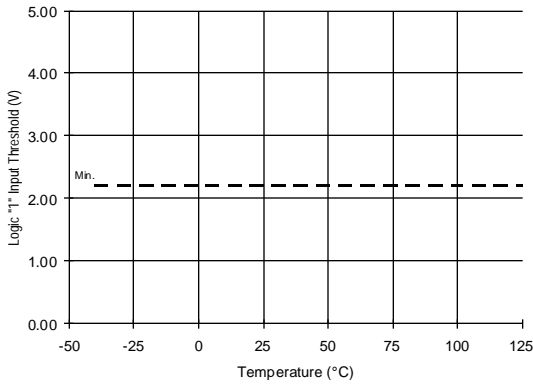


Figure 14A. Logic "1" Input Threshold vs. Temperature

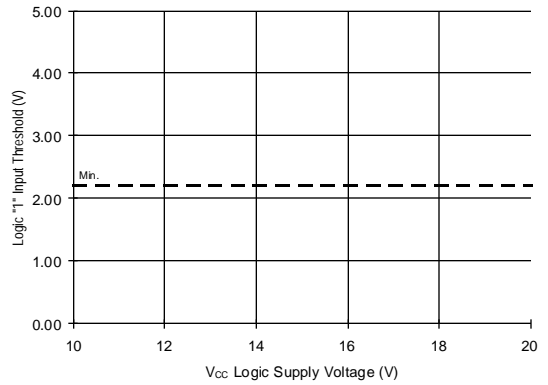


Figure 14B. Logic "1" Input Threshold vs. Voltage

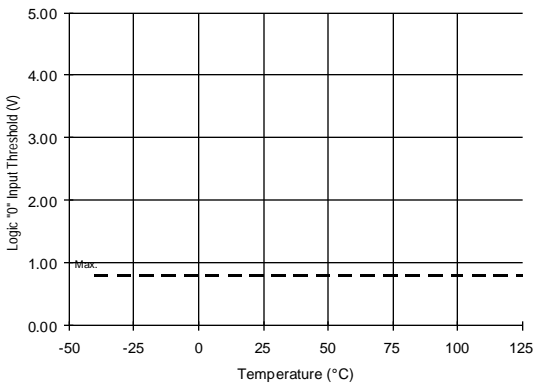


Figure 15A. Logic "0" Input Threshold vs. Temperature

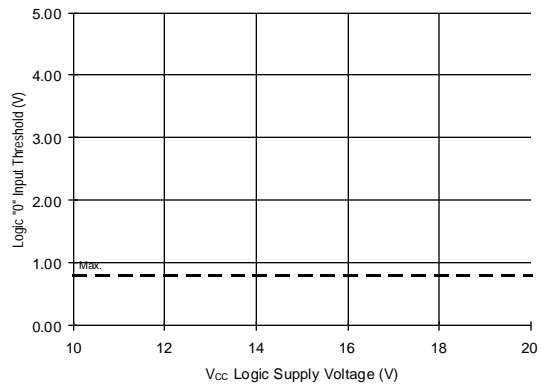


Figure 15B. Logic "0" Input Threshold vs. Voltage

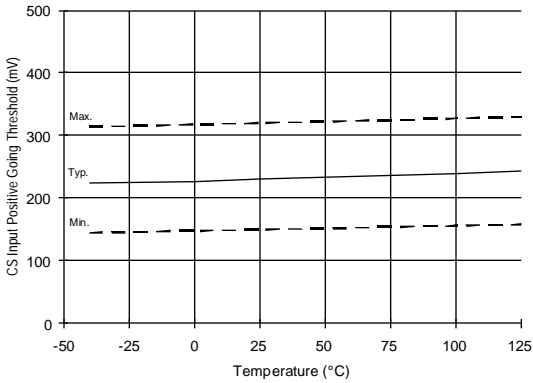


Figure 16A. CS Input Threshold (+) vs. Temperature

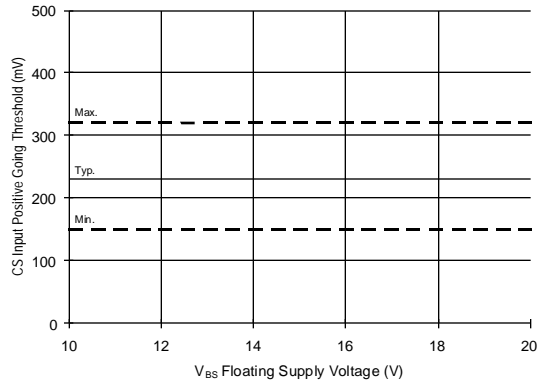


Figure 16B. CS Input Threshold (+) vs. Voltage

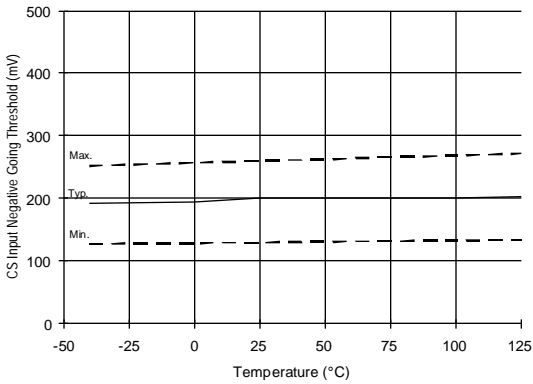


Figure 17A. CS Input Threshold (-) vs. Temperature

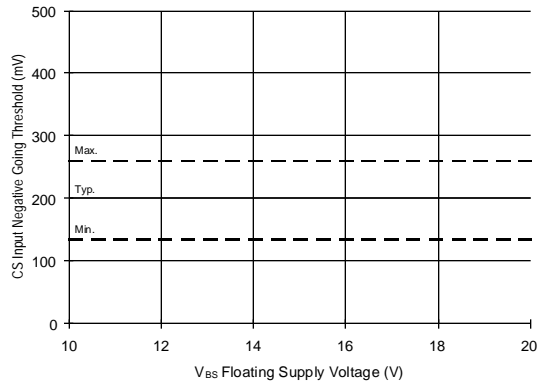


Figure 17B. CS Input Threshold (-) vs. Voltage

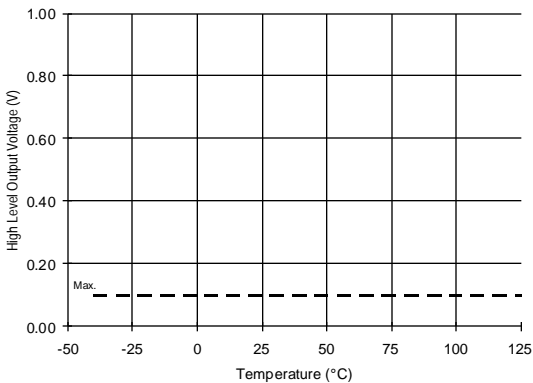


Figure 18A. High Level Output vs. Temperature

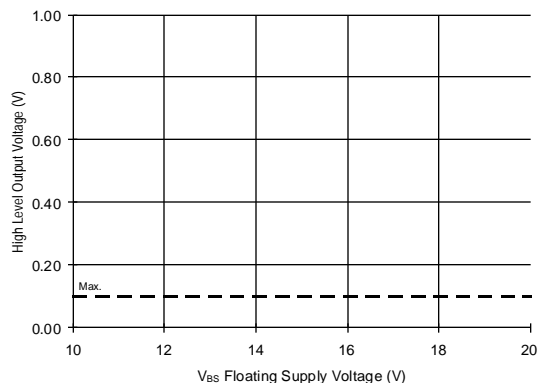


Figure 18B. High Level Output vs. Voltage

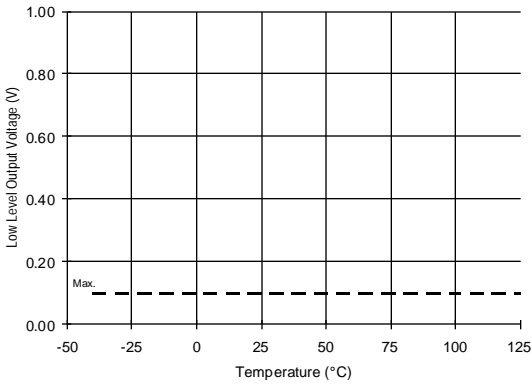


Figure 19A. Low Level Output vs. Temperature

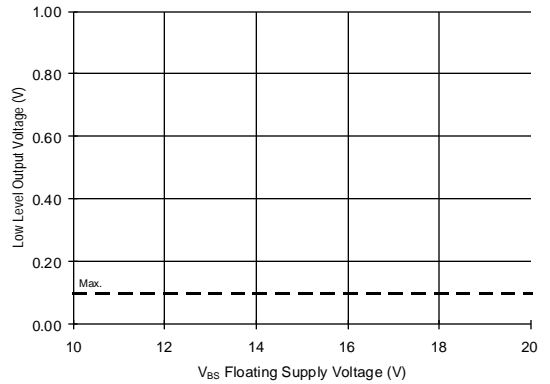


Figure 19B. Low Level Output vs. Voltage

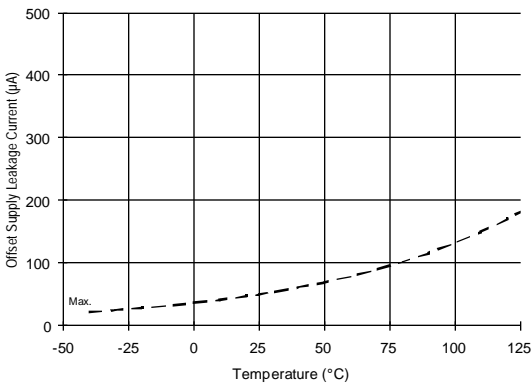


Figure 20A. Offset Supply Current vs. Temperature

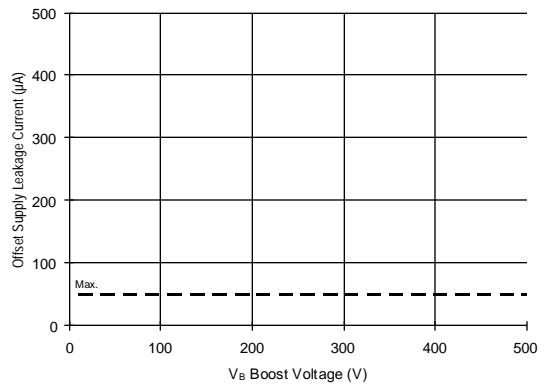


Figure 20B. Offset Supply Current vs. Voltage

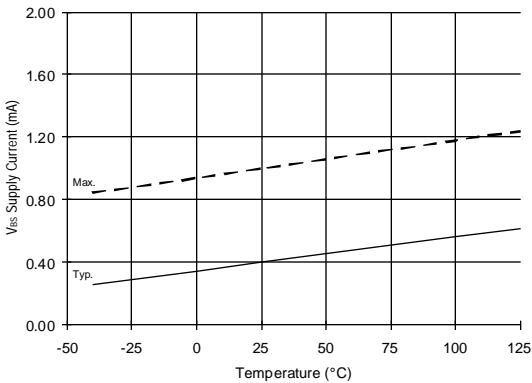


Figure 21A. V_{BS} Supply Current vs. Temperature

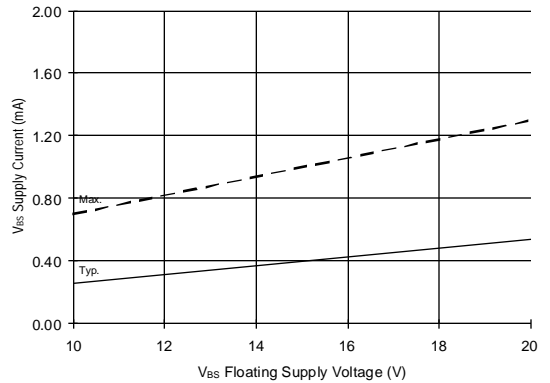


Figure 21B. V_{BS} Supply Current vs. Voltage

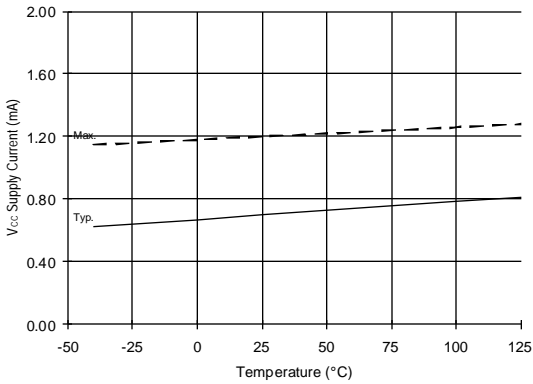


Figure 22A. V_{CC} Supply Current vs. Temperature

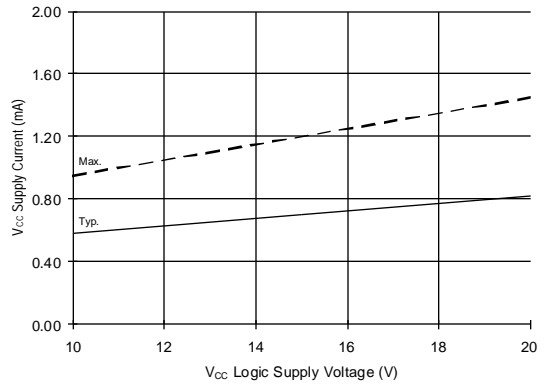


Figure 22B. V_{CC} Supply Current vs. Voltage

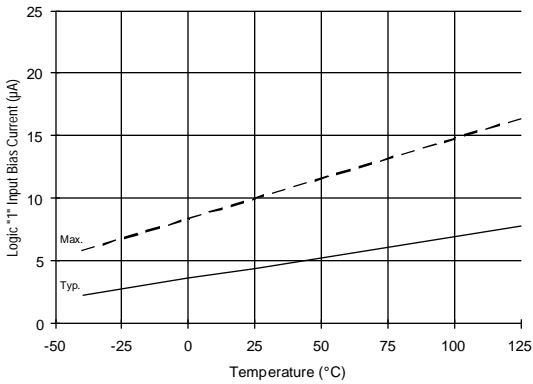


Figure 23A. Logic "1" Input Current vs. Temperature

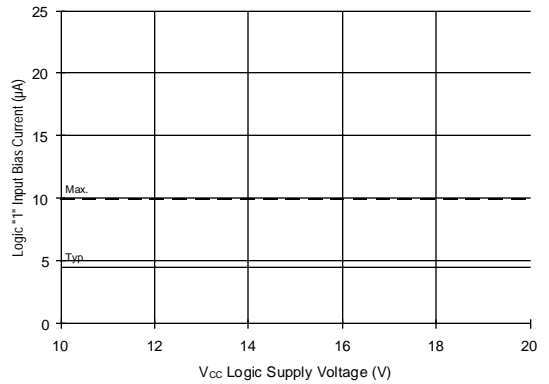


Figure 23B. Logic "1" Input Current vs. Voltage

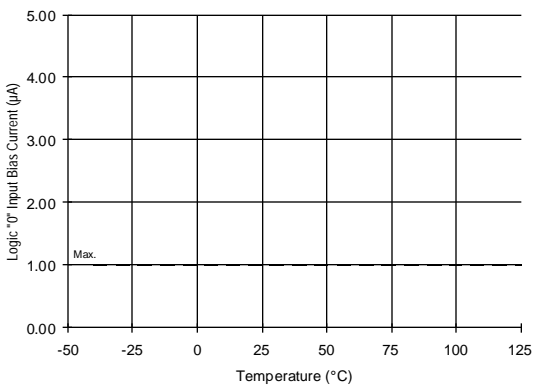


Figure 24A. Logic "0" Input Current vs. Temperature

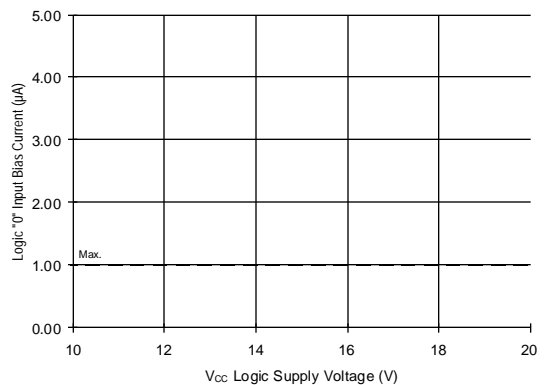


Figure 24B. Logic "0" Input Current vs. Voltage

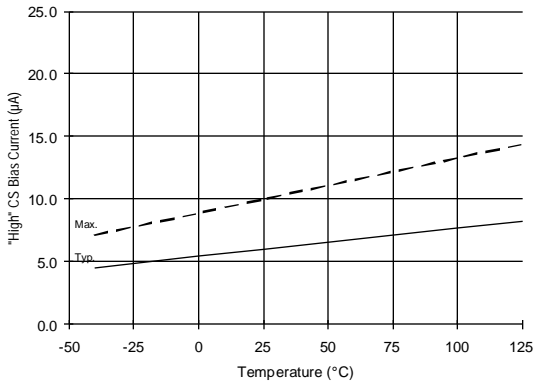


Figure 25A. "High" CS Bias Current vs. Temperature

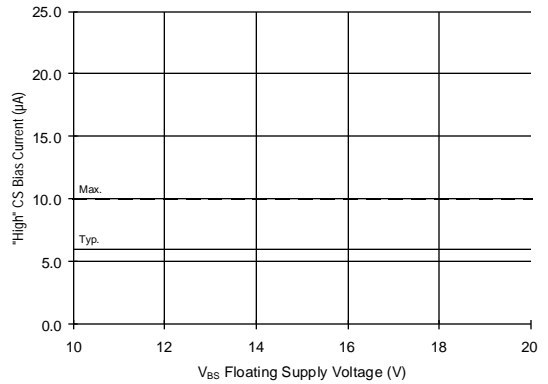


Figure 25B. "High" CS Bias Current vs. Voltage

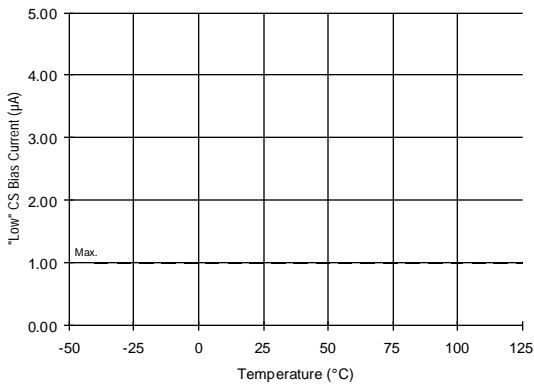


Figure 26A. "Low" CS Bias Current vs. Temperature

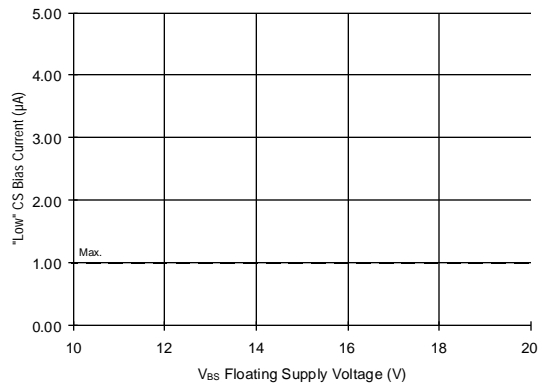


Figure 26B. "Low" CS Bias Current vs. Voltage

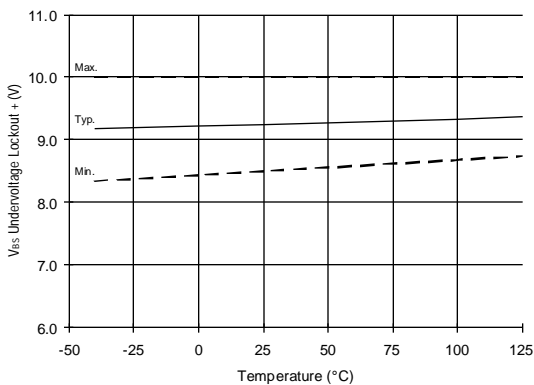


Figure 27. V_{BS} Undervoltage Lockout (+) vs. Temperature

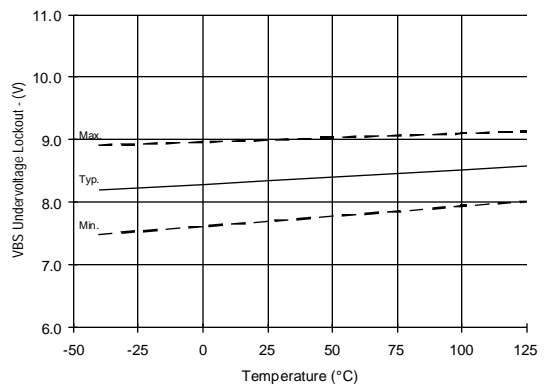


Figure 28. V_{BS} Undervoltage Lockout (-) vs. Temperature

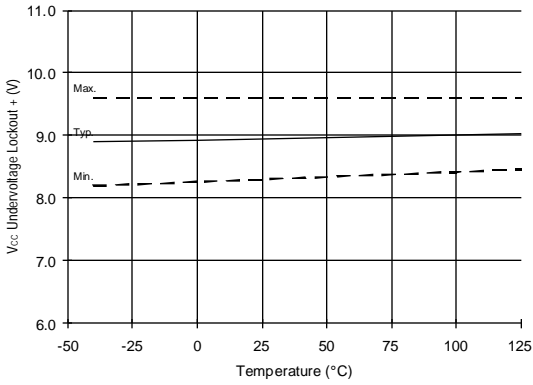


Figure 29. V_{CC} Undervoltage (+) vs. Temperature

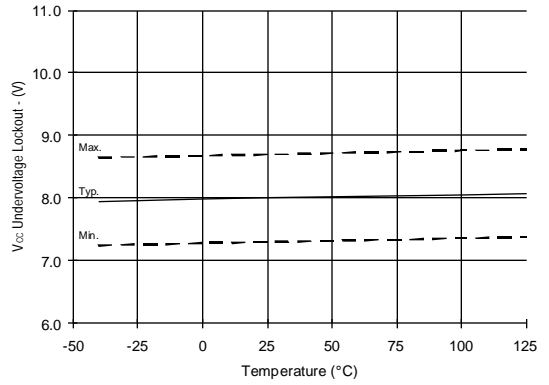


Figure 30. V_{CC} Undervoltage (-) vs. Temperature

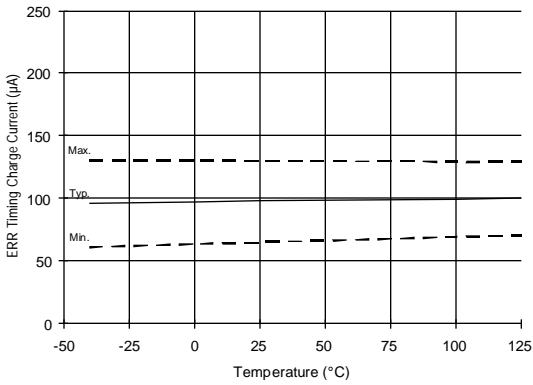


Figure 31A. ERR Timing Charge Current vs. Temperature

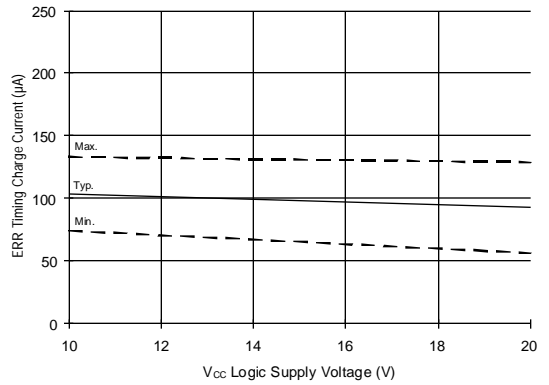


Figure 31B. ERR Timing Charge Current vs. Voltage

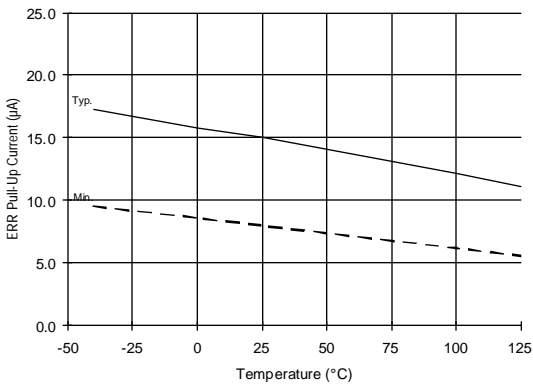


Figure 32A. ERR Pull-Up Current vs. Temperature

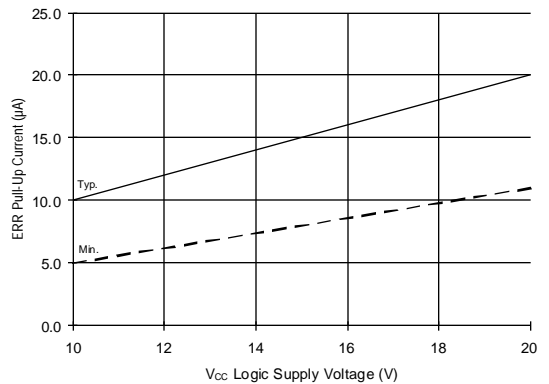


Figure 32B. ERR Pull-Up Current vs. Voltage

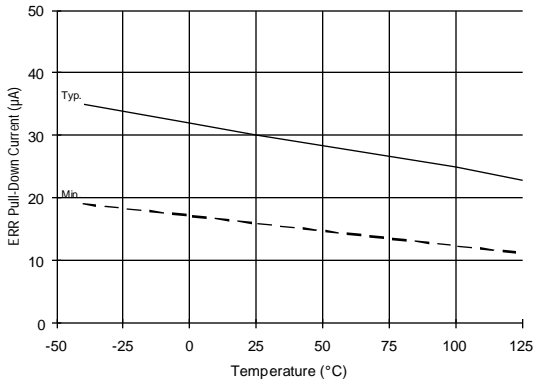


Figure 33A. ERR Pull-Down Current vs. Temperature

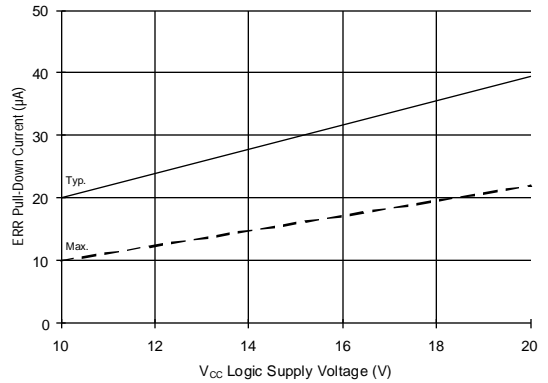


Figure 33B. ERR Pull-Down Current vs. Voltage

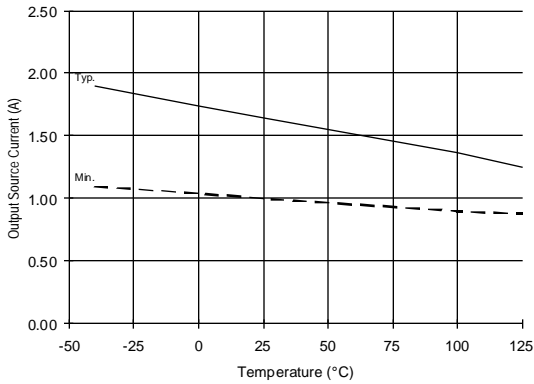


Figure 34A. Output Source Current vs. Temperature

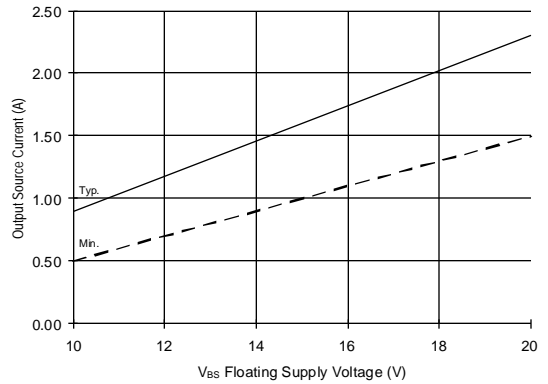


Figure 34B. Output Source Current vs. Voltage

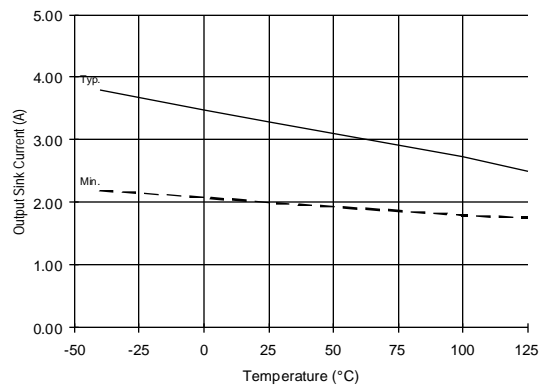


Figure 35A. Output Sink Current vs. Temperature

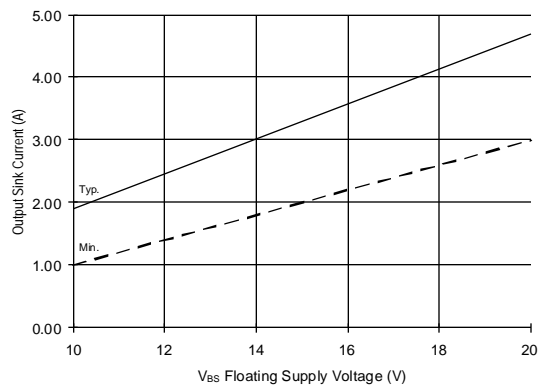


Figure 35B. Output Sink Current vs. Voltage

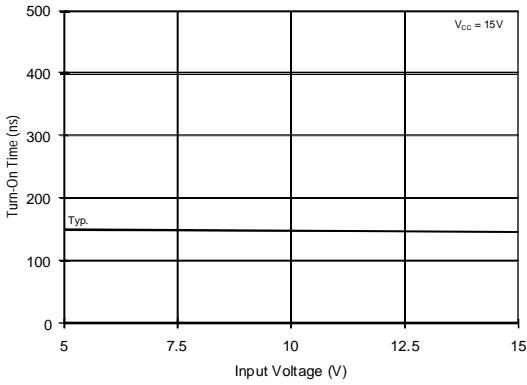


Figure 36A. Turn-On Time vs. Input Voltage

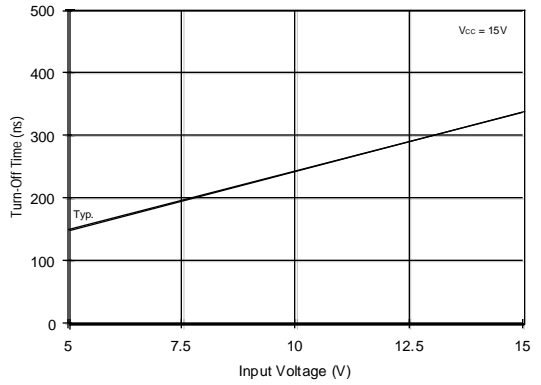


Figure 36B. Turn-Off Time vs. Input Voltage

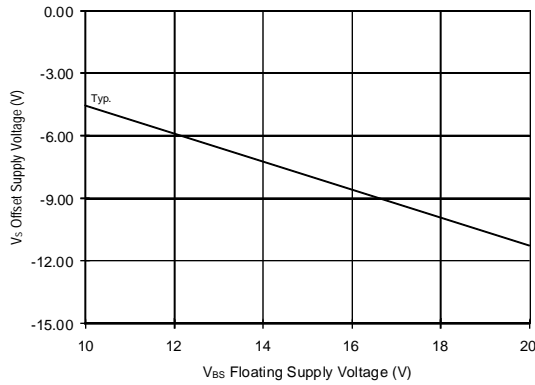


Figure 37. Maximum V_S Negative Offset vs. Supply Voltage